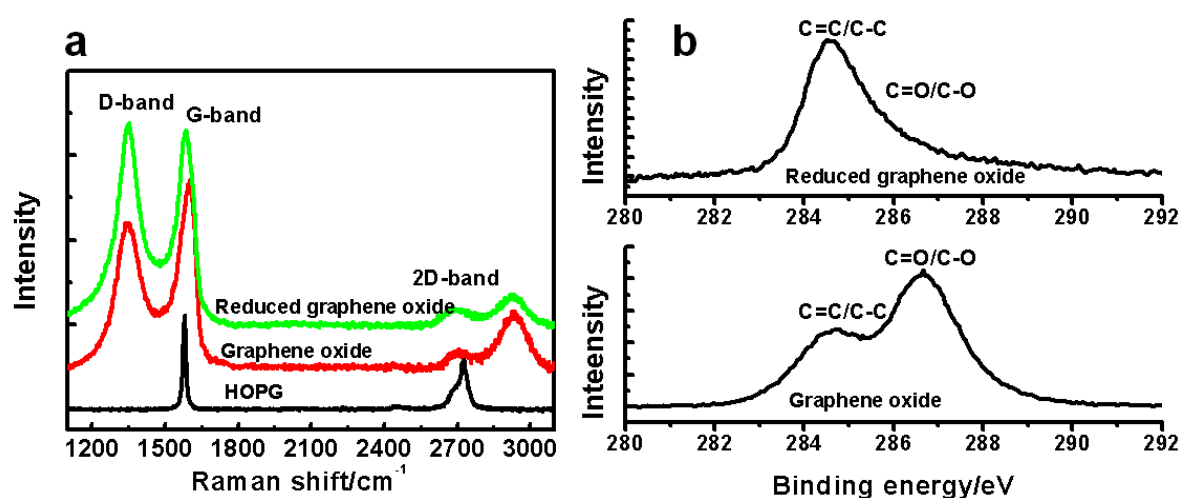


## Supplementary Information for

# Multilevel Conductance Switching for a Monolayer of Redox-Active Metal Complexes through Various Metallic Contacts

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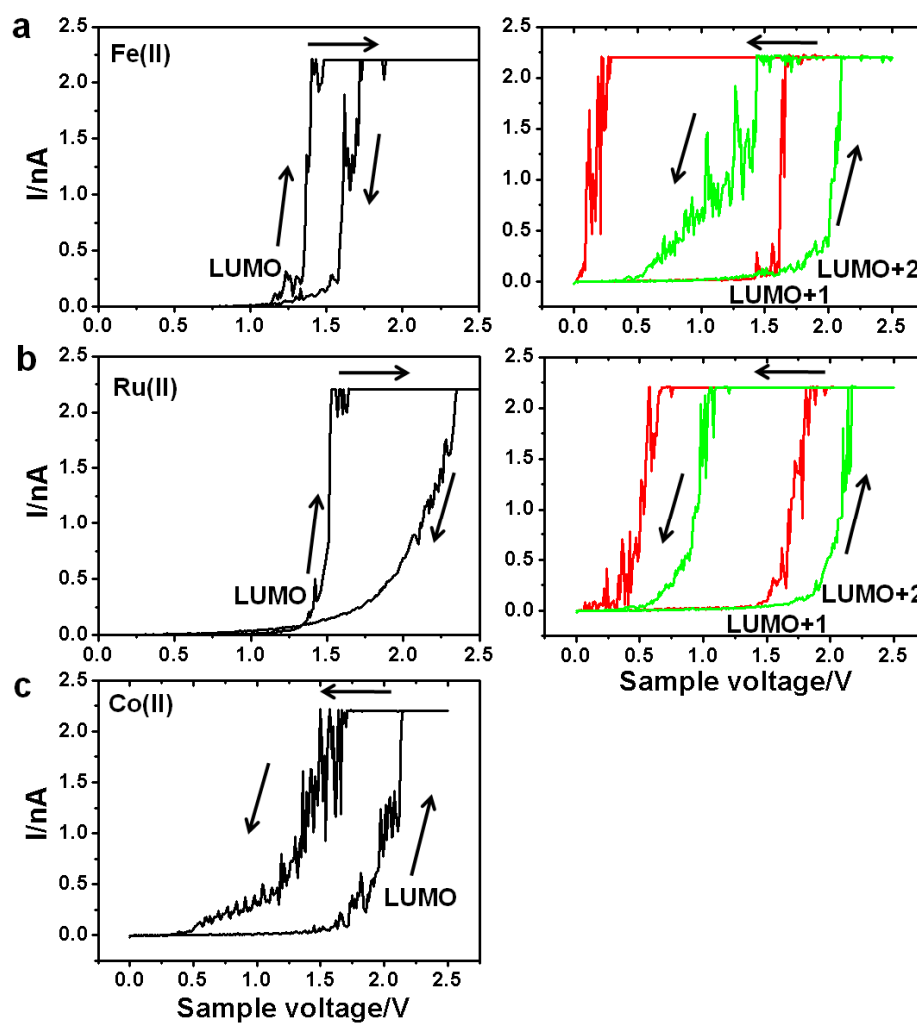
## Supplementary Figures



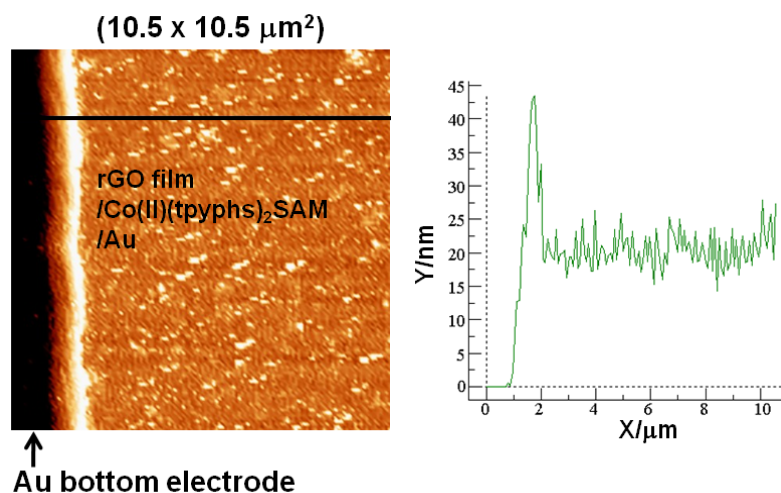
**Fig. S1.** (a) Raman spectra of highly oriented pyrolytic graphite (HOPG), graphene oxide (GO), and reduced graphene oxide (rGO). (b) XPS spectra of C 1s for rGO and GO.

In Raman spectra, the first-order G- and D-band originated from vibrations of  $sp^2$  carbon appearing at around 1600 and 1350  $cm^{-1}$ , respectively. The intensity ratio of the D and G peaks increased as GO sheets ( $D/G = 0.81$ ) converted to the rGO sheets ( $D/G = 1.02$ ). This is due to an increase in defect density corresponding to the defunctionalized epoxide and hydroxyl groups in the basal plane. Raman spectroscopy (Reinshaw, RM1000-In Via) was obtained with excitation energy of 2.41 eV (514 nm). In XPS data, one major peak was observed in rGO for carbon-carbon peak of C=C/C-C (284.6 eV) due to  $sp^2$  carbon bonding,

as carbon-oxygen peaks of C–O (286.1 eV), C=O (287.5 eV), and C(=O)–OH (289.2 eV) due to  $sp^3$  carbon bonding (in graphene oxide) was drastically diminished.

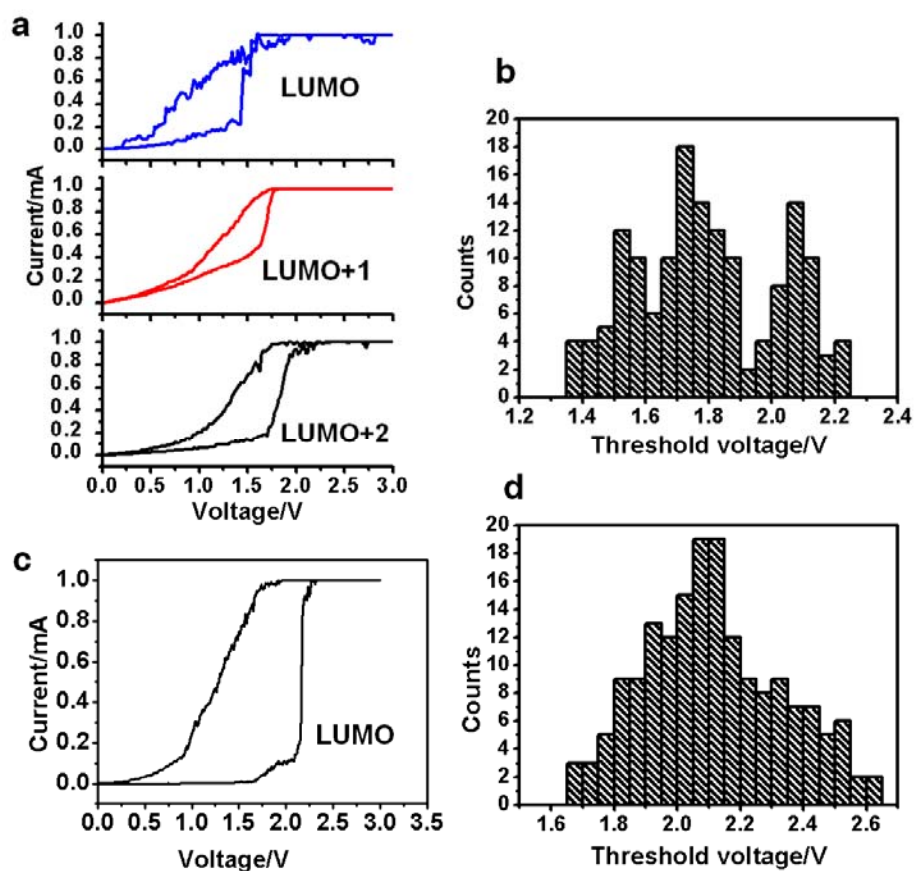


**Fig. S2.** (a)–(c)  $I/V$  curves representing conductance switching to the electron affinity levels of  $Fe^{II}$ ,  $Ru^{II}$ , and  $Co^{II}(tpyphs)_2$  complexes in STM-based junctions, respectively.



**Fig. S3.** Topographical AFM image of an rGO film on the  $\text{Co}^{\text{II}}(\text{tpyphs})_2$  SAM /gold.

Thickness of the rGO film on SAMs was measured by about 20 nm, considering the length of molecules.



**Fig. S4.** (a)  $I/V$  curves in Au/rGO film/ $\text{Ru}^{\text{II}}(\text{tpyphs})_2$  SAM/Au devices, showing three distinguishable conductance states. (b) A statistical distribution of threshold voltage for

conductance switching in Au/rGO film/ $\text{Ru}^{\text{II}}(\text{tpyphs})_2$  SAM/Au devices. (c)  $I/V$  curve in an Au/rGO film/ $\text{Co}^{\text{II}}(\text{tpyphs})_2$  SAM/Au device. (d) A statistical distribution of threshold voltage for conductance switching in Au/rGO film/ $\text{Co}^{\text{II}}(\text{tpyphs})_2$  SAM/Au devices.